

Optical and structural properties of spin coated $\text{Cu}_2\text{NiSnS}_4$ (CNTS) thin film: effect of thiourea concentration

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Introduction

In order to meet the world's increasing demands great efforts are being focused on developing low cost, non-toxic and earth abundant thin film solar cells. Various earth abundant semiconducting nanoparticles like $\text{Cu}_2\text{FeSnS}_4(\text{S}_{1-x}\text{Se}_x)$ (CZTSSe), $\text{Cu}_2\text{ZnSnS}_4$ (CZTS), $\text{Cu}_2\text{FeSnS}_4$ (CFTS), $\text{Cu}_2\text{CoSnS}_4$ (CCTS) and $\text{Cu}_2\text{NiSnS}_4$ (CNTS) have much attention as absorber layer for thin film solar cells due to their suitable direct band gap and high absorption coefficients (10^4 to 10^5 cm^{-1}) [1]. However, the CNTS films have recently been successfully used in photovoltaic applications using different deposition techniques such as electro deposition [2], solvothermal [3], spray technique [4], thermal chemical decomposition [5] and hot injection method [6]. Given the importance of CNTS in many applications and in many areas, we have considered the effect of sulfur (thiourea) concentration in the CNTS films by spin coating method.

Objectives

1. CNTS thin film samples such as CNTS-6M, CNTS-8M, CNTS-10M and CNTS-12M have been prepared
2. Optical properties such as absorbance, transmittance, absorption coefficient and band gap of the prepared CNTS thin films have been studied and compared with the prepared thin films.
3. Structural properties of the developed CNTS thin film have been analyzed.
4. Micro-structural properties have also been determined.

Thin Film Deposition Technology

CNTS thin films were deposited by spin coating technique starting with non-aqueous solution. This non-aqueous solutions were prepared by dissolving copper chloride dihydrate (2M), nickelchloride hexahydrate (1M), tin chloride dihydrate (1M) and thiourea (6M, 8M, 10M, 12M) in 2-methoxyethanol and a few drops of monoethanolamine (MEA) and then stirred at 50 degree for an hour. The resulted solutions were deposited onto soda lime glass substrates by spin coating with a rotation speed of 1400 rpm for 30s. After first coating, the substrates were preheated at 150 degree for 10 min to evaporate the solvents and these coating processes were repeated for four times to get required thickness of the films. Finally dense CNTS films were annealed at 340 degree for 30 min.

Prepared Samples & Characterization Equipments

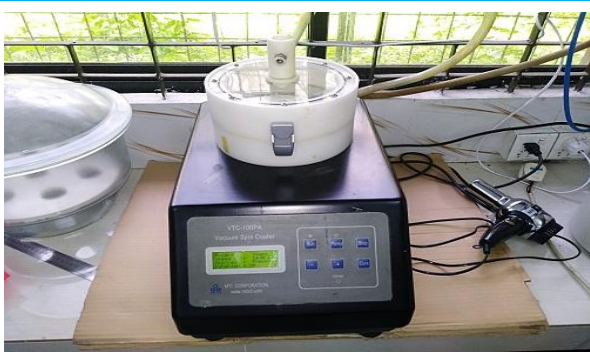


Fig. 1: Spin Coater



Fig. 2: Furnace



Fig. 3: Prepared CNTS thin films



Fig. 4: UV-visible Spectrometer



Fig. 5: X-ray diffractometer

Results

Absorbance Measurements

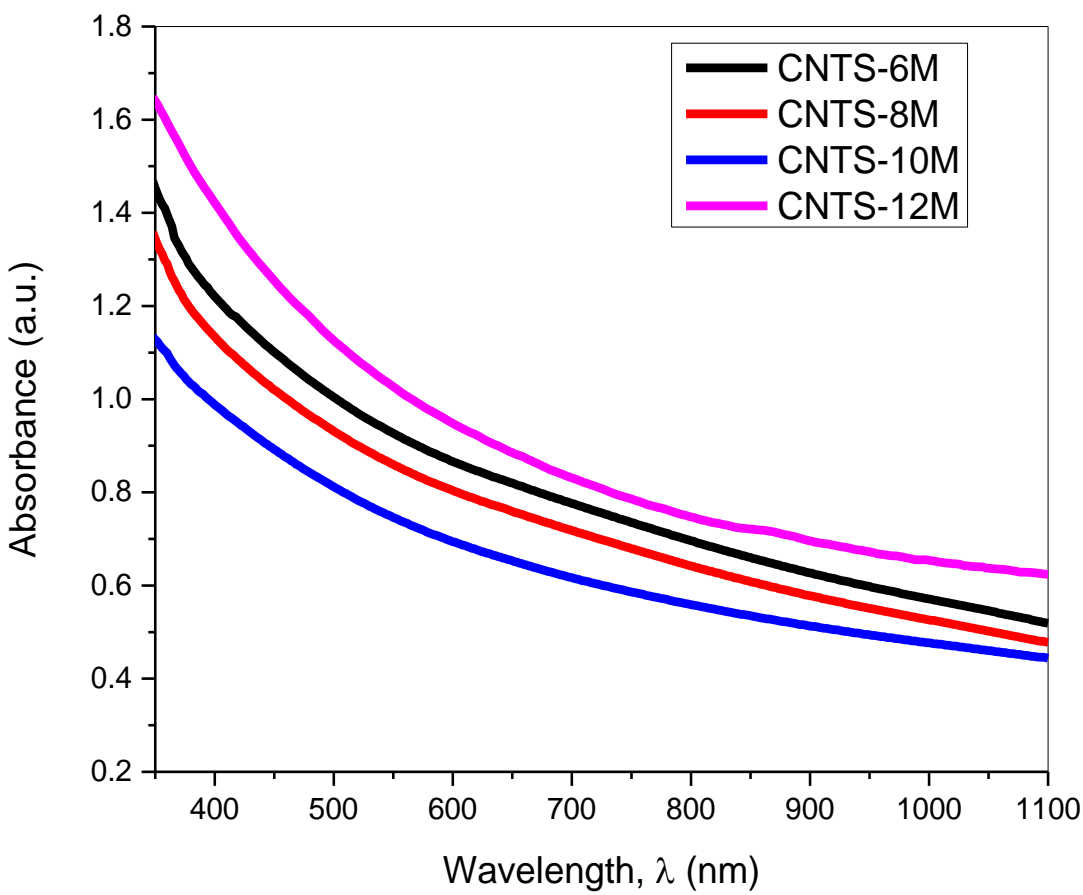


Fig. 6: Absorbance versus wavelength graphs of different types of CNTS thin films show maximum absorbance for CNTS-12M and also exhibit inverse relationship between the absorbance and the wavelength.

Transmittance(%) Measurements

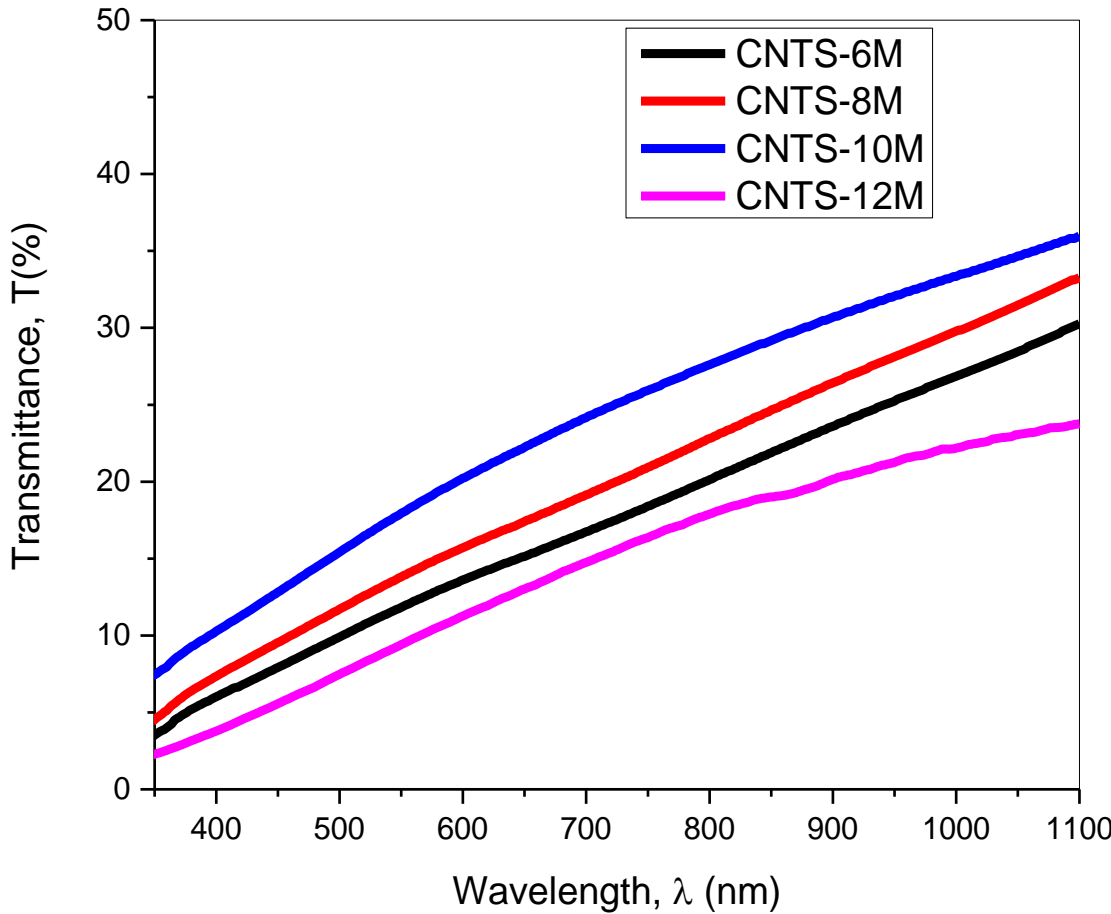


Fig. 7: Transmittance(%) versus wavelength graphs of different types of CNTS thin films show minimum transmittance(%) for CNTS-12M and also exhibit linear relationship between the absorbance and the wavelength.

Absorption Coefficient Measurements

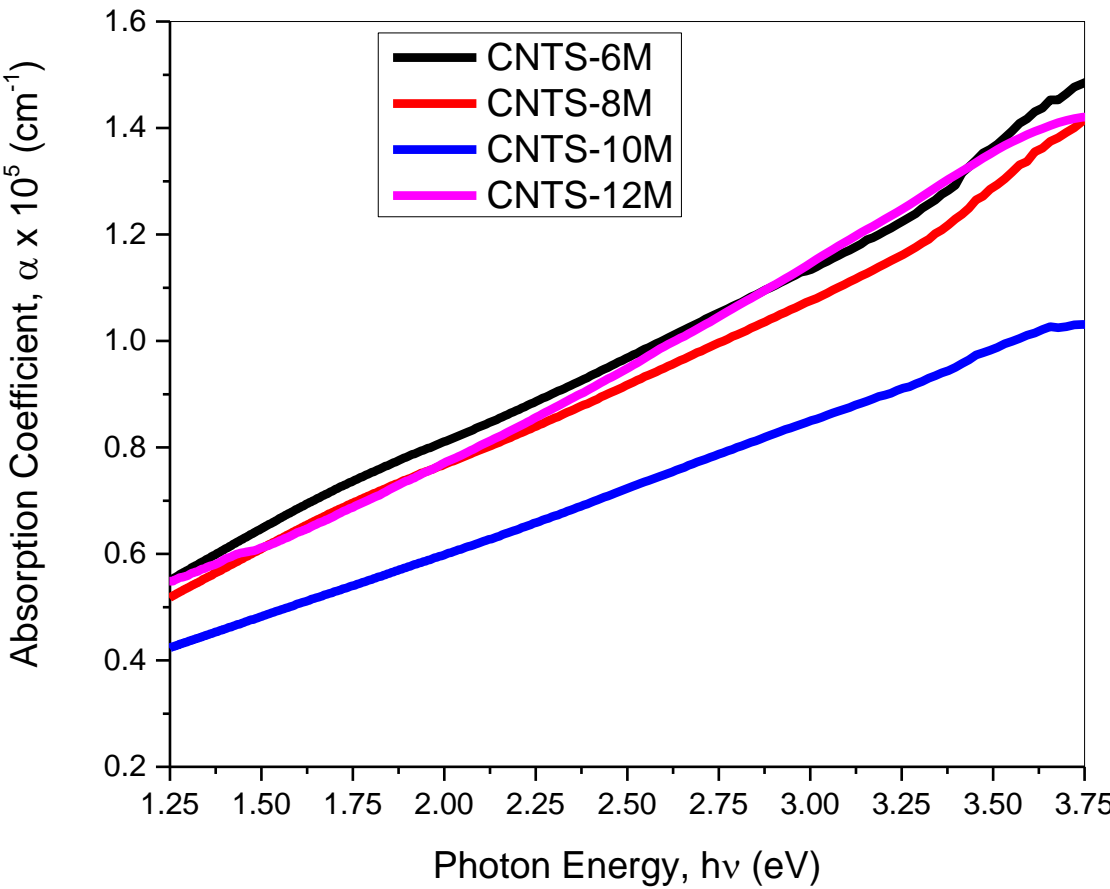


Fig. 8: Absorption coefficient versus wavelength graphs of different types of CNTS thin films show maximum absorption coefficient ($1.27 \times 10^5 \text{ cm}^{-1}$) for CNTS-12M in visible region and also exhibit linear relationship between the absorption coefficient and the photon energy.

Optical Band Gap Measurements

Table 01:

Sample Name	CNTS-6M	CNTS-8M	CNTS-10M	CNTS-12M
Band Gap (eV)	2.83	2.86	2.62	2.56

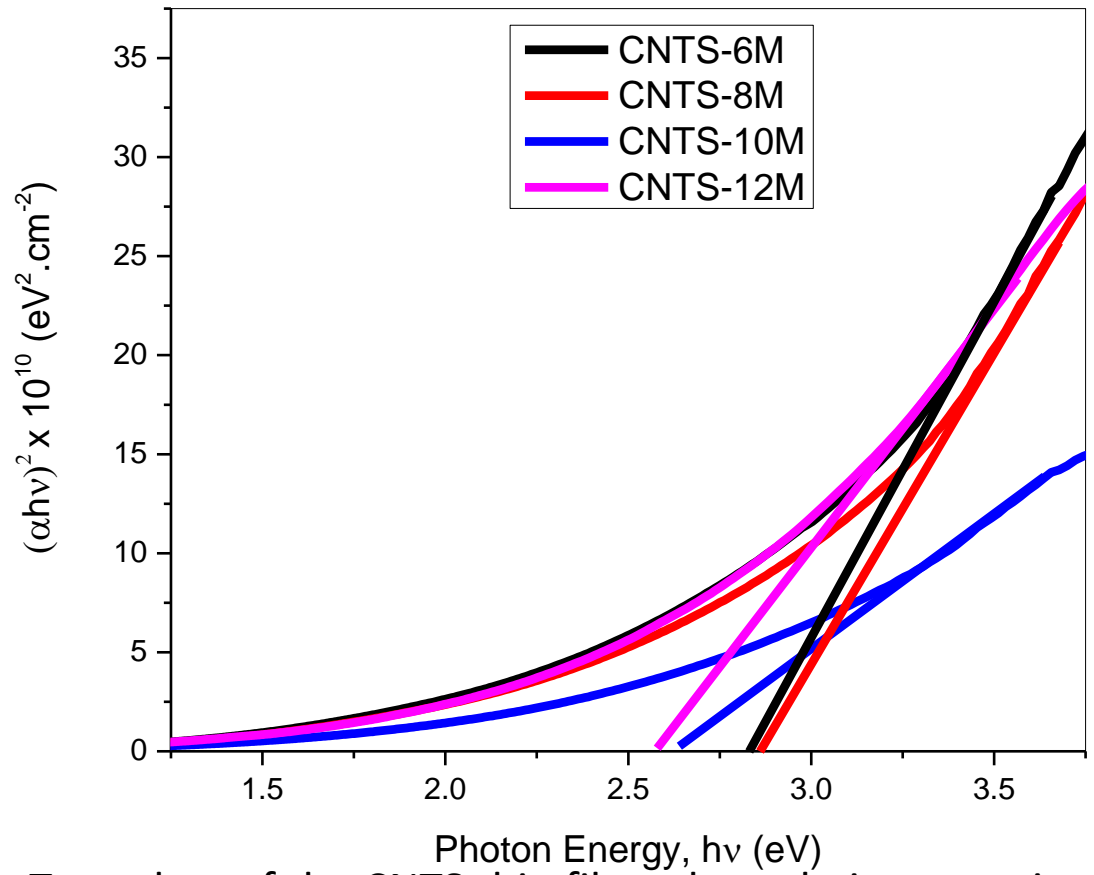


Fig. 9: Tauc plots of the CNTS thin films show their respective band gaps

X-ray diffraction (XRD) Measurements

Table 02: Grain properties of the CNTS thin films for the prominent peak (111)

Sample Name	FWHM (deg.)	Crystallite size (nm)	Dislocation density (line/nm^2)	Micro-strain* 10^-3	Lattice parameter (Å)
CNTS-6M	1.0331	7.93	0.0159	4.4	5.42
CNTS-8M	1.1313	7.24	0.0191	4.8	5.42
CNTS-10M	1.0010	8.19	0.0149	4.2	5.40
CNTS-12M	0.7581	10.81	0.0086	3.2	5.42

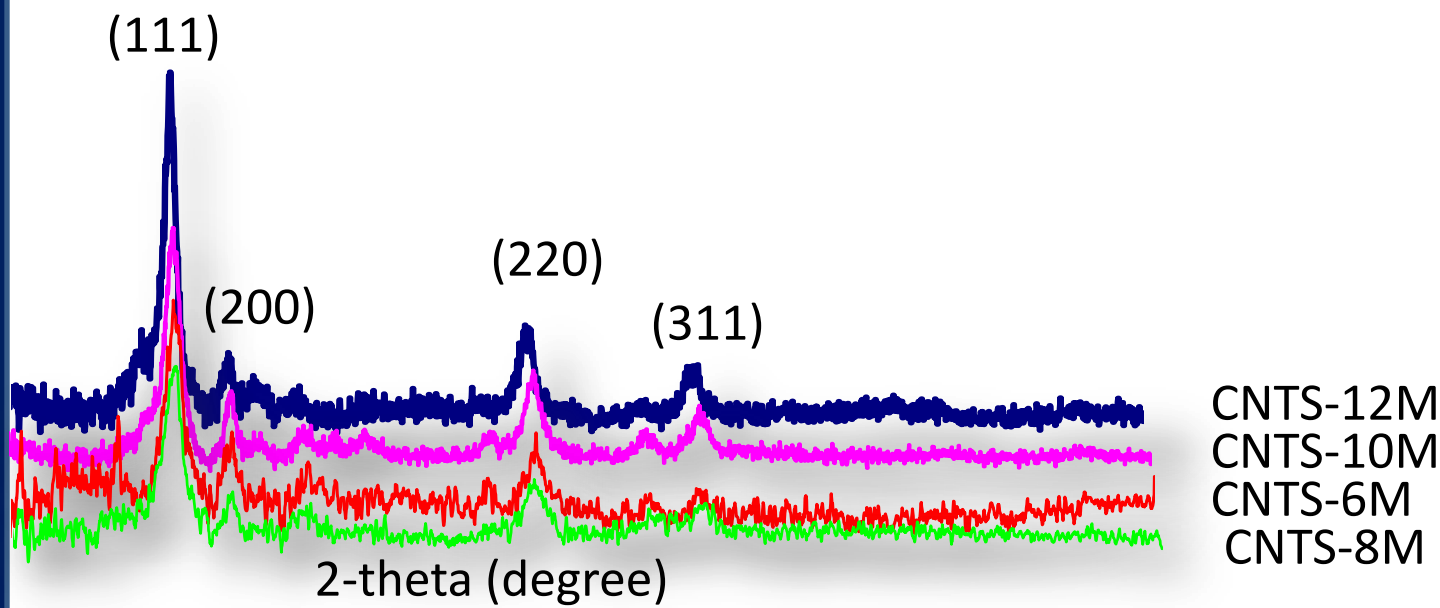


Fig. 10 : XRD pattern of CNTS thin films confirms cubic structure

Conclusion

From our investigation we may conclude that CNTS-12M thin film is more suitable for solar cell applications due to its higher absorbance, lower transmittance(%), higher absorption coefficient, lower band gap energy and better crystalline quality with low dislocation density than the other three thin films (CNTS-6M, CNTS-8M & CNTS-10M).

References

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